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April 1st, 2010 Renesas Electronics Corporation

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MOS FIELD EFFECT TRANSISTOR $\mu PA2701TP$

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The μ PA2701TP, which has a heat spreader, is N-Channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of notebook computers.

FEATURES

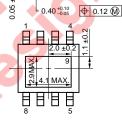
- Low on-state resistance RDS(on)1 = 7.5 m Ω MAX. (VGS = 10 V, ID = 7.0 A) RDS(on)2 = 11.6 m Ω MAX. (VGS = 4.5 V, ID = 7.0 A)
- Low Ciss: Ciss = 1200 pF TYP. (VDS = 10 V, VGS = 0 V)
- Small and surface mount package (Power HSOP8)

ORDERING INFORMATION

| PART NUMBER | PACKAGE | |
|-------------|-------------|--|
| μPA2701TP | Power HSOP8 | |

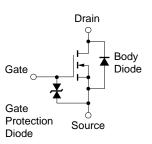
1, 2, 3 : Source 4 : Gate 5, 6, 7, 8, 9 : Drain 6.0 ± 0.3 1, 27 TYP: Sign of the second of the sec

PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C, Unless otherwise noted, All terminals are connected.)

| Drain to Source Voltage (Vgs = 0 V) | VDSS | 30 | V |
|---|---------------------|-------------|----|
| Gate to Source Voltage (Vps = 0 V) | Vgss | ±20 | V |
| Drain Current (DC) (Tc = 25°C) | ID(DC)1 | ±35 | Α |
| Drain Current (DC) (T _A = 25°C) Note1 | I _{D(DC)2} | ±16 | Α |
| Drain Current (pulse) Note2 | D(pulse) | ±80 | Α |
| Total Power Dissipation (Tc = 25°C) | P _{T1} | 28 | W |
| Total Power Dissipation (T _A = 25°C) Note1 | P _{T2} | 3 | W |
| Channel Temperature | Tch | 150 | °C |
| Storage Temperature | T_{stg} | -55 to +150 | °C |
| Single Avalanche Current Note3 | I AS | 18 | Α |
| Single Avalanche Energy Note3 | Eas | 32.4 | mJ |



EQUIVALENT CIRCUIT

- **Notes 1.** Mounted on a glass epoxy board (1 inch x 1 inch x 0.8 mm), PW = 10 sec
 - **2.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - 3. Starting Tch = 25°C, VdD = 15 V, Rg = 25 Ω , L = 100 μ H, Vgs = 20 \rightarrow 0 V

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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ELECTRICAL CHARACTERISTICS (TA = 25°C, Unless otherwise noted, All terminals are connected.)

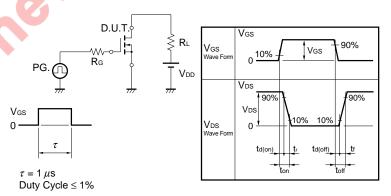
| CHARACTERISTICS | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------------------------------|----------------------|--|------|------|------|------|
| Zero Gate Voltage Drain Current | IDSS | Vps = 30 V, Vgs = 0 V | | | 10 | μΑ |
| Gate Leakage Current | Igss | V _G S = ±20 V, V _D S = 0 V | | | ±10 | μΑ |
| Gate Cut-off Voltage | V _{GS(off)} | V _{DS} = 10 V, I _D = 1 mA | 1.5 | 2.0 | 2.5 | V |
| Forward Transfer Admittance | yfs | V _{DS} = 10 V, I _D = 7.0 A | 7 | 14 | | S |
| Drain to Source On-state Resistance | RDS(on)1 | Vgs = 10 V, Ip = 7.0 A | | 6.2 | 7.5 | mΩ |
| | RDS(on)2 | Vgs = 4.5 V, ID = 7.0 A | | 8.7 | 11.6 | mΩ |
| | RDS(on)3 | Vgs = 4.0 V, ID = 7.0 A | | 10.3 | 13.7 | mΩ |
| Input Capacitance | Ciss | V _{DS} = 10 V | | 1200 | | pF |
| Output Capacitance | Coss | Vgs = 0 V | | 500 | | pF |
| Reverse Transfer Capacitance | Crss | f = 1 MHz | | 160 | | pF |
| Turn-on Delay Time | td(on) | V _{DD} = 15 V, I _D = 7.0 A | | 10 | | ns |
| Rise Time | tr | Vgs = 10 V | | 13 | | ns |
| Turn-off Delay Time | t d(off) | R _G = 10 Ω | | 44 | | ns |
| Fall Time | tf | | | 11 | | ns |
| Total Gate Charge | Q _G | V _{DD} = 15 V | | 12 | | nC |
| Gate to Source Charge | Qgs | Vgs = 5 V | | 4 | | nC |
| Gate to Drain Charge | Q _{GD} | ID = 14 A | _ | 6 | | nC |
| Body Diode Forward Voltage | V _{F(S-D)} | IF = 14 A, Vgs = 0 V | | 0.8 | 1.2 | V |
| Reverse Recovery Time | trr | I _F = 14 A, V _G s = 0 V | | 32 | | ns |
| Reverse Recovery Charge | Qrr | $di/dt = 100 A/ \mu s$ | | 27 | | nC |

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$R_{G} = 25 \Omega$ $V_{GS} = -20 \rightarrow 0 V$ $R_{G} = 25 \Omega$ V_{DD} V_{DD} V_{DD} V_{DD} V_{DD} V_{DD}

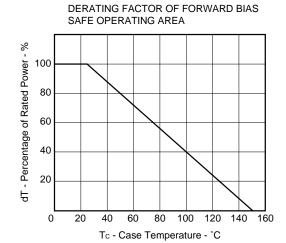
-Starting Tch

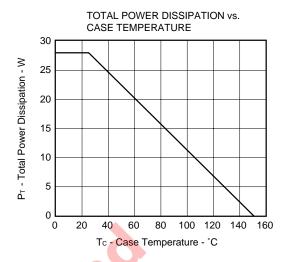
TEST CIRCUIT 2 SWITCHING TIME



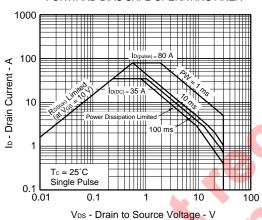
TEST CIRCUIT 3 GATE CHARGE

TYPICAL CHARACTERISTICS (TA = 25°C)



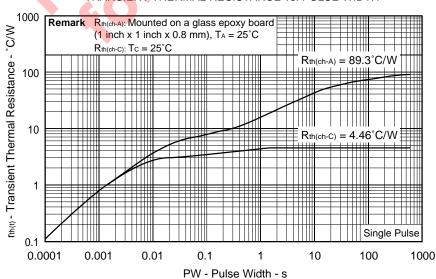


FORWARD BIAS SAFE OPERATING AREA



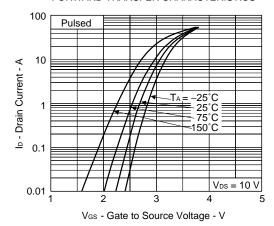
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

MACSI

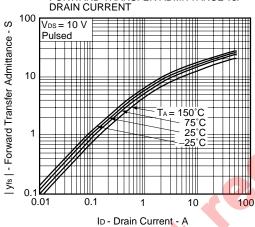


3

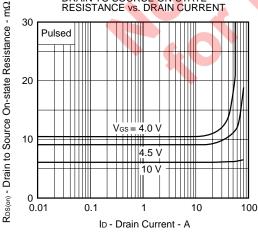
FORWARD TRANSFER CHARACTERISTICS



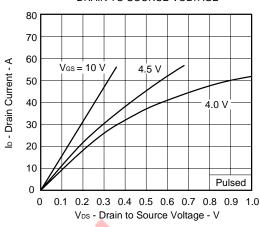
FORWARD TRANSFER ADMITTANCE vs.



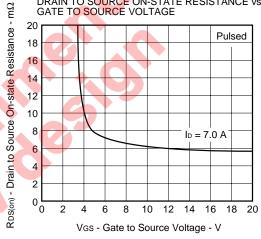
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



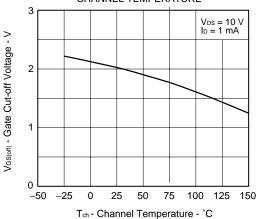
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

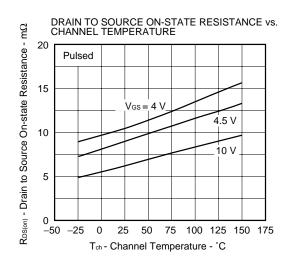


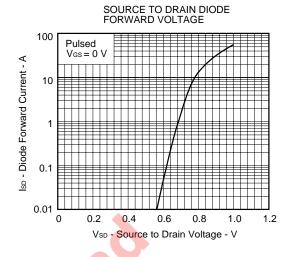
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

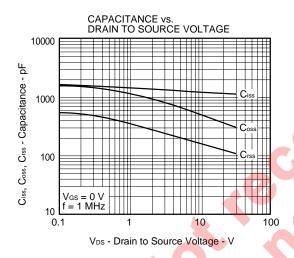


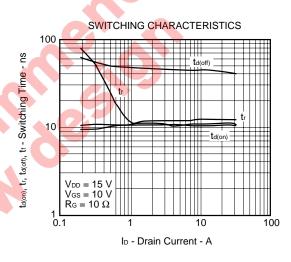
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

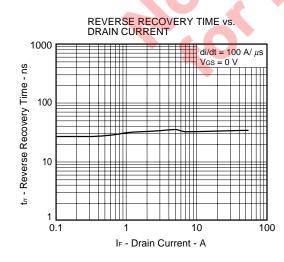


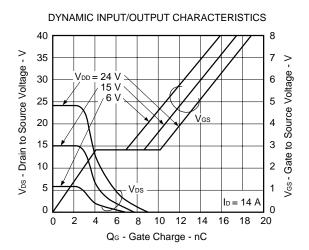












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